

SMD1 (TO-276AB) PACKAGE

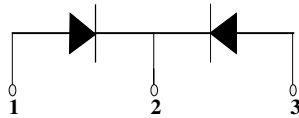
SiC SCHOTTKY DIODE



V_R 300V
 I_F 2x10A

Semelab's Silicon Carbide (SiC) Schottky diodes exhibit low forward voltage, zero reverse recovery, and superb high-temperature performance.

The devices employ Semelab's proven hermetic packaging technology and are suitable for high-frequency hard-switching applications, where system efficiency and reliability are paramount.



ABSOLUTE MAXIMUM RATINGS at $T_J = 25^\circ\text{C}$ unless otherwise stated (per leg)

Symbol	Parameter	Rating	Units
V_R	DC Reverse Voltage	300	V
V_{RRM}	Repetitive Peak Reverse Voltage	300	V
V_{RSM}	Surge Peak Reverse Voltage	300	V
I_F	DC Forward Current $T_C = 100^\circ\text{C}$	10	A
I_{FRM}	Repetitive Peak Forward Current $T_J = 150^\circ\text{C}$, $T_C = 100^\circ\text{C}$, $D = 0.1$	45	A
I_{FSM}	Surge Peak Forward Current $T_C = 25^\circ\text{C}$, $t_p = 10\mu\text{s}$	100	A
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	70W	W
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$

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